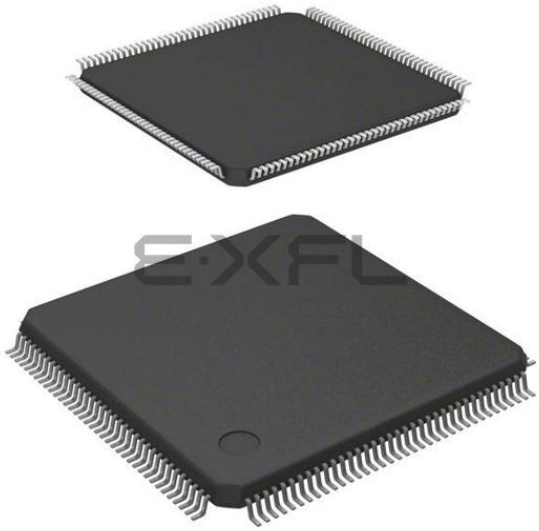

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, I²C, IrDA, LINbus, MMC, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	100K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f205zct7

1 Introduction

This datasheet provides the description of the STM32F205xx and STM32F207xx lines of microcontrollers. For more details on the whole STMicroelectronics STM32 family, please refer to *Section 2.1: Full compatibility throughout the family*.

The STM32F205xx and STM32F207xx datasheet should be read in conjunction with the STM32F20x/STM32F21x reference manual. They will be referred to as STM32F20x devices throughout the document.

For information on programming, erasing and protection of the internal Flash memory, please refer to the STM32F20x/STM32F21x Flash programming manual (PM0059).

The reference and Flash programming manuals are both available from the STMicroelectronics website *www.st.com*.

For information on the Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the *www.arm.com* website.

2.1 Full compatibility throughout the family

The STM32F205xx and STM32F207xx constitute the STM32F20x family whose members are fully pin-to-pin, software and feature compatible, allowing the user to try different memory densities and peripherals for a greater degree of freedom during the development cycle.

The STM32F205xx and STM32F207xx devices maintain a close compatibility with the whole STM32F10xxx family. All functional pins are pin-to-pin compatible. The STM32F205xx and STM32F207xx, however, are not drop-in replacements for the STM32F10xxx devices: the two families do not have the same power scheme, and so their power pins are different. Nonetheless, transition from the STM32F10xxx to the STM32F20x family remains simple as only a few pins are impacted.

Figure 1, *Figure 2* and *Figure 3* provide compatible board designs between the STM32F20x and the STM32F10xxx family.

Figure 1. Compatible board design between STM32F10xx and STM32F2xx for LQFP64 package

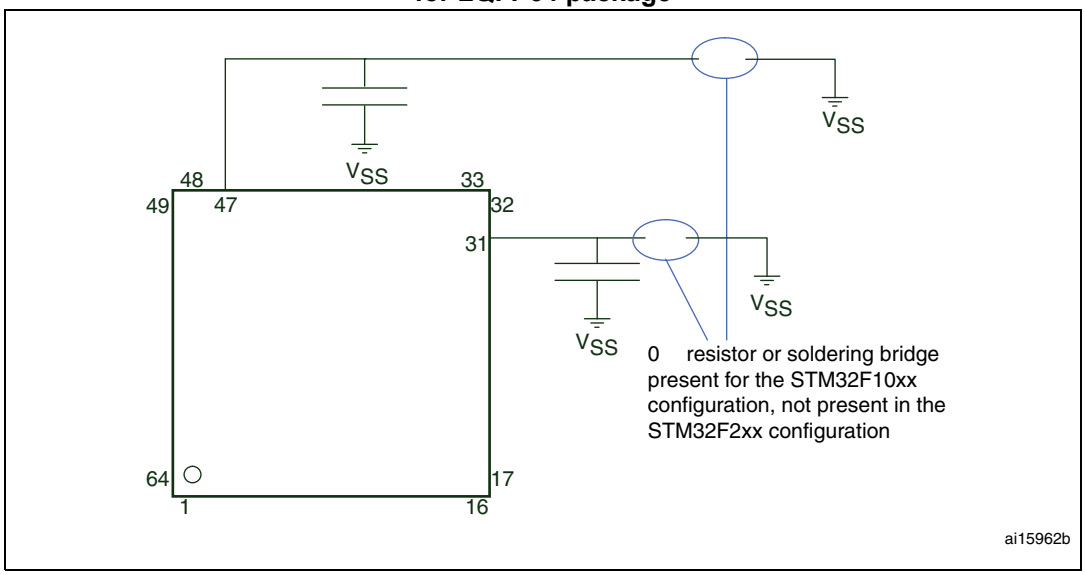


Figure 2. Compatible board design between STM32F10xx and STM32F2xx for LQFP100 package

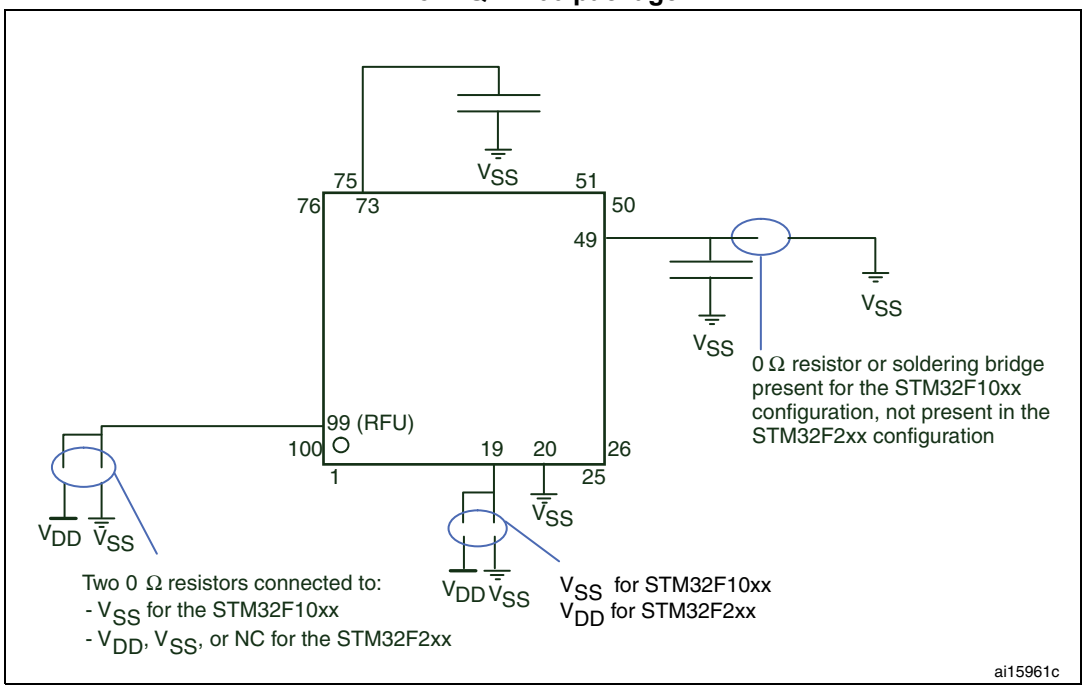
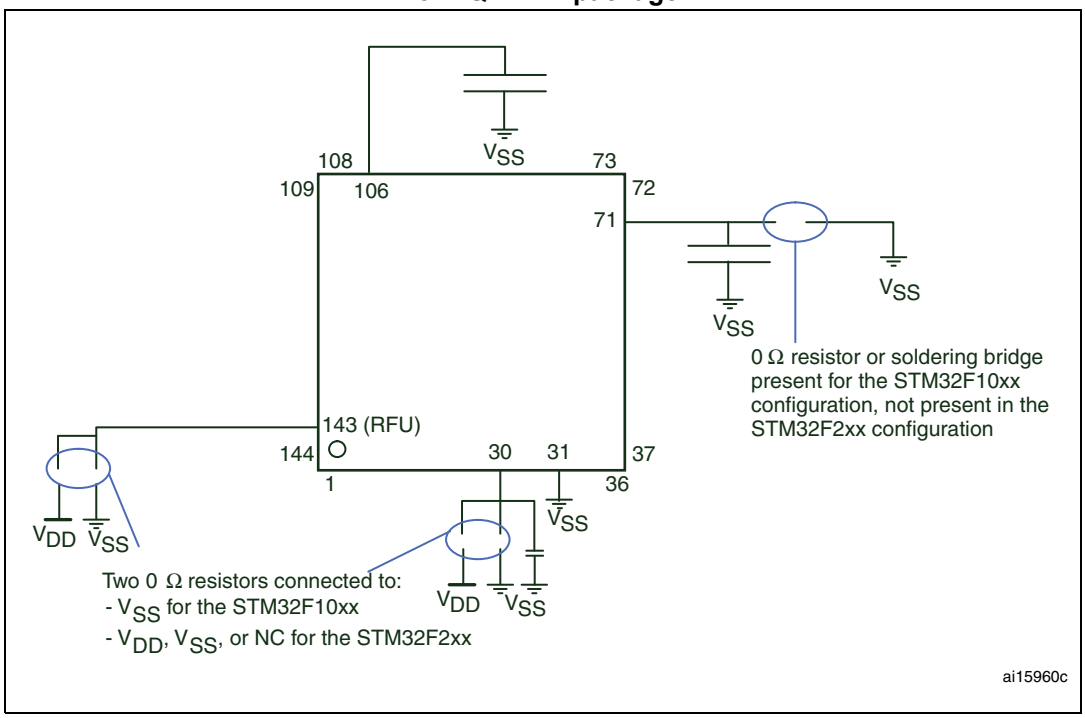


Figure 3. Compatible board design between STM32F10xx and STM32F2xx for LQFP144 package



1. RFU = reserved for future use.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see *Section 3.18: Low-power modes*).

Like backup SRAM, the RTC and backup registers are supplied through a switch that is powered either from the V_{DD} supply when present or the V_{BAT} pin.

3.18 Low-power modes

The STM32F20x family supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The device can be woken up from the Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup or the Ethernet wakeup.

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

  The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped when the device enters the Stop or Standby mode.

3.19 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery or an external supercapacitor.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When using WLCSP64+2 package, if IRROFF pin is connected to V_{DD}, the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

Table 8. STM32F20x pin and ball definitions (continued)

Pins						Pin name (function after reset)[1]	Pin type	I/O structure	Note	Alternate functions	Additional functions
LQFP64	WLCSP64+2	LQFP100	LQFP144	LQFP176	UFBGA176						
-	-	98	142	170	A3	PE1	I/O	FT	-	FSMC_NBL1, DCMI_D3, EVENTOUT	-
-	-	-	-	-	D5	V_{SS}	S	-	-	-	-
63	D8	-	-	-	-	V_{SS}	S	-	-	-	-
-	-	99	143	171	C6	RFU	-	-	(7)	-	-
64	D9	100	144	172	C5	V_{DD}	S	-	-	-	-
-	-	-	-	173	D4	PI4	I/O	FT	-	TIM8_BKIN, DCMI_D5, EVENTOUT	-
-	-	-	-	174	C4	PI5	I/O	FT	-	TIM8_CH1, DCMI_VSYNC, EVENTOUT	-
-	-	-	-	175	C3	PI6	I/O	FT	-	TIM8_CH2, DCMI_D6, EVENTOUT	-
-	-	-	-	176	C2	PI7	I/O	FT	-	TIM8_CH3, DCMI_D7, EVENTOUT	-
-	C8	-	-	-	-	IRROFF	I/O	-	-	-	-

1. Function availability depends on the chosen device.
2. PC13, PC14, PC15 and PI8 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 and PI8 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these I/Os must not be used as a current source (e.g. to drive an LED).
3. Main function after the first backup domain power-up. Later on, it depends on the contents of the RTC registers even after reset (because these registers are not reset by the main reset). For details on how to manage these I/Os, refer to the RTC register description sections in the STM32F20x and STM32F21x reference manual, available from the STMicroelectronics website: www.st.com.
4. FT = 5 V tolerant except when in analog mode or oscillator mode (for PC14, PC15, PH0 and PH1).
5. If the device is delivered in an UFBGA176 package and if the REGOFF pin is set to V_{DD} (Regulator OFF), then PA0 is used as an internal Reset (active low).
6. FSMC_NL pin is also named FSMC_NADV on memory devices.
7. RFU means “reserved for future use”. This pin can be tied to V_{DD},V_{SS} or left unconnected.

Table 9. FSMC pin definition

Pins	FSMC				LQFP100
	CF	NOR/PSRAM/SRAM	NOR/PSRAM Mux	NAND 16 bit	
PE2	-	A23	A23	-	Yes
PE3	-	A19	A19	-	Yes
PE4	-	A20	A20	-	Yes

5 Memory mapping

The memory map is shown in *Figure 16*.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are configured as analog inputs by firmware.
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 30 MHz, 1 wait state from 30 to 60 MHz, 2 wait states from 60 to 90 MHz and 3 wait states from 90 to 120 MHz).
- When the peripherals are enabled HCLK is the system clock, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$, except is explicitly mentioned.
- The maximum values are obtained for V_{DD} = 3.6 V and maximum ambient temperature (T_A), and the typical values for T_A= 25 °C and V_{DD} = 3.3 V unless otherwise specified.

Table 20. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM (1)

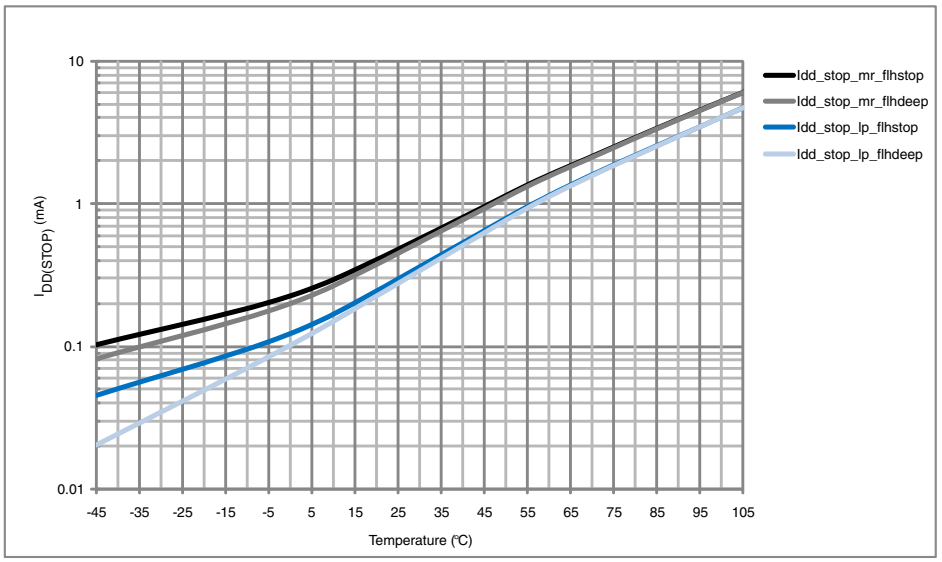
Symbol	Parameter	Conditions	f_{HCLK}	Typ	Max(2)		Unit
				T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Run mode	External clock(3), all peripherals enabled(4)	120 MHz	49	63	72	mA
			90 MHz	38	51	61	
			60 MHz	26	39	49	
			30 MHz	14	27	37	
			25 MHz	11	24	34	
			16 MHz(5)	8	21	30	
			8 MHz	5	17	27	
			4 MHz	3	16	26	
			2 MHz	2	15	25	
		External clock(3), all peripherals disabled	120 MHz	21	34	44	
			90 MHz	17	30	40	
			60 MHz	12	25	35	
			30 MHz	7	20	30	
			25 MHz	5	18	28	
			16 MHz(5)	4.0	17.0	27.0	
			8 MHz	2.5	15.5	25.5	
			4 MHz	2.0	14.7	24.8	
			2 MHz	1.6	14.5	24.6	

1. Code and data processing running from SRAM1 using boot pins.
2. Guaranteed by characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
3. External clock is 4 MHz and PLL is on when f_{HCLK} > 25 MHz.
4. When the ADC is on (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.
5. In this case HCLK = system clock/2.

Table 23. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max			Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD_STOP}	Supply current in Stop mode with main regulator in Run mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.55	1.2	11.00	20.00	mA
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.50	1.2	11.00	20.00	
	Supply current in Stop mode with main regulator in Low-power mode	Flash in Stop mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.35	1.1	8.00	15.00	
		Flash in Deep power down mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	0.30	1.1	8.00	15.00	

Figure 29. Typical current consumption vs. temperature in Stop mode



1. All typical and maximum values from table 18 and figure 26 will be reduced over time by up to 50% as part of ST continuous improvement of test procedures. New versions of the datasheet will be released to reflect these changes

Table 30. HSE 4-26 MHz oscillator characteristics(1) (2)

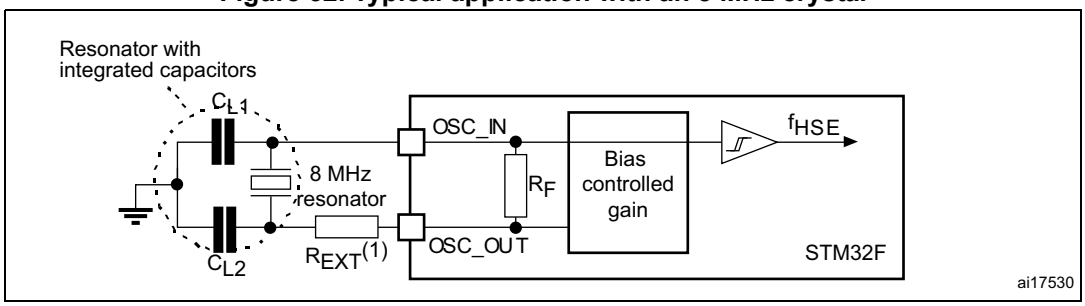
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	4	-	26	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	V_{DD}=3.3 V, ESR= 30 Ω, C_L=5 pF@25 MHz	-	449	-	µA
		V_{DD}=3.3 V, ESR= 30 Ω, C_L=10 pF@25 MHz	-	532	-	
g_m	Oscillator transconductance	Startup	5	-	-	mA/V
$t_{SU(HSE}$(3)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by characterization results, not tested in production.
3. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 32*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 32. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 31*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

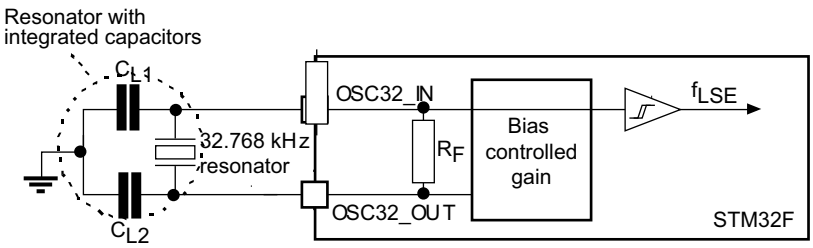
Table 31. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_F	Feedback resistor	-	-	18.4	-	MΩ
I_{DD}	LSE current consumption	-	-	-	1	µA
g_m	Oscillator Transconductance	-	2.8	-	-	µA/V
$t_{SU(LSE)}$ (2)	startup time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design, not tested in production.
2. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

Note: For information on electing the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 33. Typical application with a 32.768 kHz crystal



6.3.9 Internal clock source characteristics

The parameters given in *Table 32* and *Table 33* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Table 32. HSI oscillator characteristics (1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user-trimming step(2)	-	-	-	1	%
	Accuracy of the HSI oscillator	T_A = –40 to 105 °C(3)	– 8	-	4.5	%
		T_A = –10 to 85 °C(3)	– 4	-	4	%
		T_A = 25 °C(4)	– 1	-	1	%
$t_{su(HSI)}$ (2)	HSI oscillator startup time	-	-	2.2	4.0	µs
$I_{DD(HSI)}$ (2)	HSI oscillator power consumption	-	-	60	80	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.
3. Guaranteed by characterization results.
4. Factory calibrated, parts not soldered.

Table 35. PLLI2S (audio PLL) characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Jitter(3)	Master I2S clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-	ps
			peak to peak	-	±280	-	
		Average frequency of 12.288 MHz N=432, R=5 on 1000 samples		-	90	-	ps
	WS I2S clock jitter	Cycle to cycle at 48 KHz on 1000 samples		-	400	-	ps
$I_{DD(PLLI2S)}$(4)	PLLI2S power consumption on V_{DD}	VCO freq = 192 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLI2S)}$(4)	PLLI2S power consumption on V_{DDA}	VCO freq = 192 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design, not tested in production.
3. Value given with main PLL running.
4. Guaranteed by characterization results, not tested in production.

Table 39. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Double word programming	T_A = 0 to +40 °C V_{DD} = 3.3 V V_{PP} = 8.5 V	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
t_{VPP}(3)	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design, not tested in production.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 40. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Guaranteed by characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

Table 46. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
R_{PU}	Weak pull-up equivalent resistor(6)	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{SS}$	30	40	50	kΩ
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	
R_{PD}	Weak pull-down equivalent resistor(7)	All pins except for PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	$V_{IN} = V_{DD}$	30	40	50	
		PA10/PB12 (OTG_FS_ID, OTG_HS_ID)	-	7	10	14	
C_{IO}(8)	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design, not tested in production.
2. Guaranteed by tests in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to *Table 45: I/O current injection susceptibility*
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to *Table 45: I/O current injection susceptibility*
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).
7. Pull-down resistors are designed with a true resistance in series with a switchable NMOS. This NMOS contribution to the series resistance is minimum (~10% order).
8. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements for FT I/Os is shown in *Figure 38*.

Table 51. Characteristics of TIMx connected to the APB2 domain(1)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APB2 prescaler distinct from 1, $f_{TIMxCLK}$ = 120 MHz	1	-	$t_{TIMxCLK}$
			8.3	-	ns
		AHB/APB2 prescaler = 1, $f_{TIMxCLK}$ = 60 MHz	1	-	$t_{TIMxCLK}$
			16.7	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK}$ = 120 MHz APB2 = 60 MHz	0	$f_{TIMxCLK}/2$	MHz
			0	60	MHz
Res_{TIM}	Timer resolution		-	16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected		1	65536	$t_{TIMxCLK}$
			0.0083	546	µs
t_{MAX_COUNT}	Maximum possible count		-	65536 × 65536	$t_{TIMxCLK}$
			-	35.79	s

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

6.3.19 Communications interfaces

I^2C interface characteristics

STM32F205xx and STM32F207xx I^2C interface meets the requirements of the standard I^2C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I^2C characteristics are described in *Table 52*. Refer also to *Section 6.3.16: I/O port characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).

6.3.20 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 66* are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in *Table 14*.

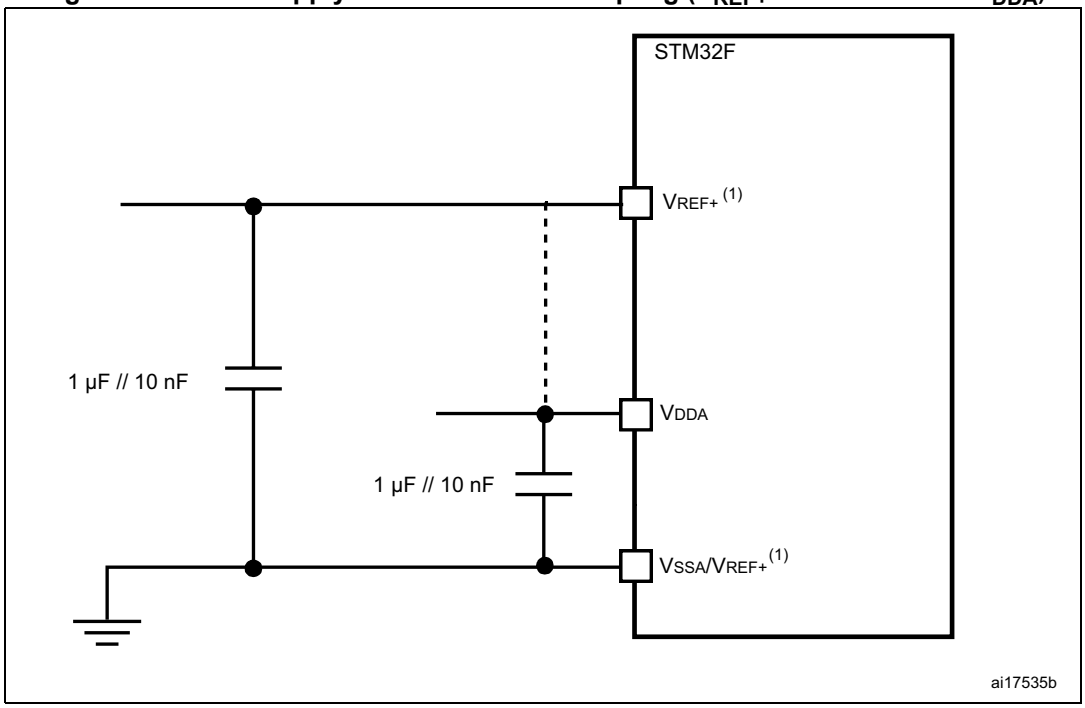
Table 66. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Power supply	-	1.8(1)	-	3.6	V
V_{REF+}	Positive reference voltage	-	1.8(1)(2)	-	V_{DDA}	V
f_{ADC}	ADC clock frequency	V_{DDA} = 1.8(1) to 2.4 V	0.6	-	15	MHz
		V_{DDA} = 2.4 to 3.6 V	0.6	-	30	MHz
f_{TRIG}(3)	External trigger frequency	f_{ADC} = 30 MHz with 12-bit resolution	-	-	1764	kHz
		-	-	-	17	$1/f_{ADC}$
V_{AIN}	Conversion voltage range(4)	-	0 (V_{SSA} or V_{REF-} tied to ground)	-	V_{REF+}	V
R_{AIN}(3)	External input impedance	See *Equation 1* for details	-	-	50	kΩ
R_{ADC}(3)(5)	Sampling switch resistance	-	1.5	-	6	kΩ
C_{ADC}(3)	Internal sample and hold capacitor	-	-	4	-	pF
t_{lat}(3)	Injection trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.100	µs
		-	-	-	3(6)	$1/f_{ADC}$
t_{latr}(3)	Regular trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.067	µs
		-	-	-	2(6)	$1/f_{ADC}$
t_S(3)	Sampling time	f_{ADC} = 30 MHz	0.100	-	16	µs
		-	3	-	480	$1/f_{ADC}$
t_{STAB}(3)	Power-up time	-	-	2	3	µs
t_{CONV}(3)	Total conversion time (including sampling time)	f_{ADC} = 30 MHz 12-bit resolution	0.5	-	16.40	µs
		f_{ADC} = 30 MHz 10-bit resolution	0.43	-	16.34	µs
		f_{ADC} = 30 MHz 8-bit resolution	0.37	-	16.27	µs
		f_{ADC} = 30 MHz 6-bit resolution	0.3	-	16.20	µs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 54* or *Figure 55*, depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 54. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176 package. V_{REF+} is also available on all packages except for LQFP64. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

Table 76. Synchronous multiplexed NOR/PSRAM read timings(1)(2) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{su(ADV-CLKH)}$	FSMC_A/D[15:0] valid data before FSMC_CLK high	5	-	ns
$t_{h(CLKH-ADV)}$	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results, not tested in production.

Figure 62. Synchronous multiplexed PSRAM write timings

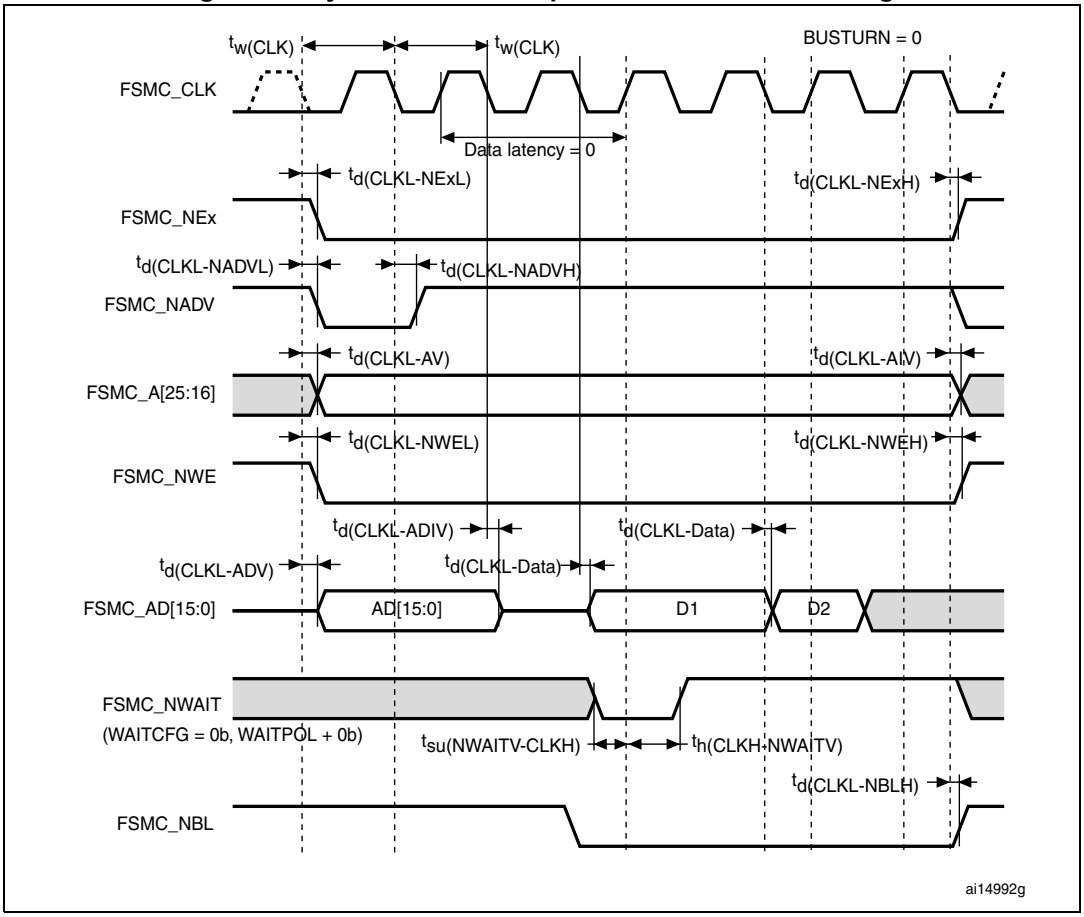
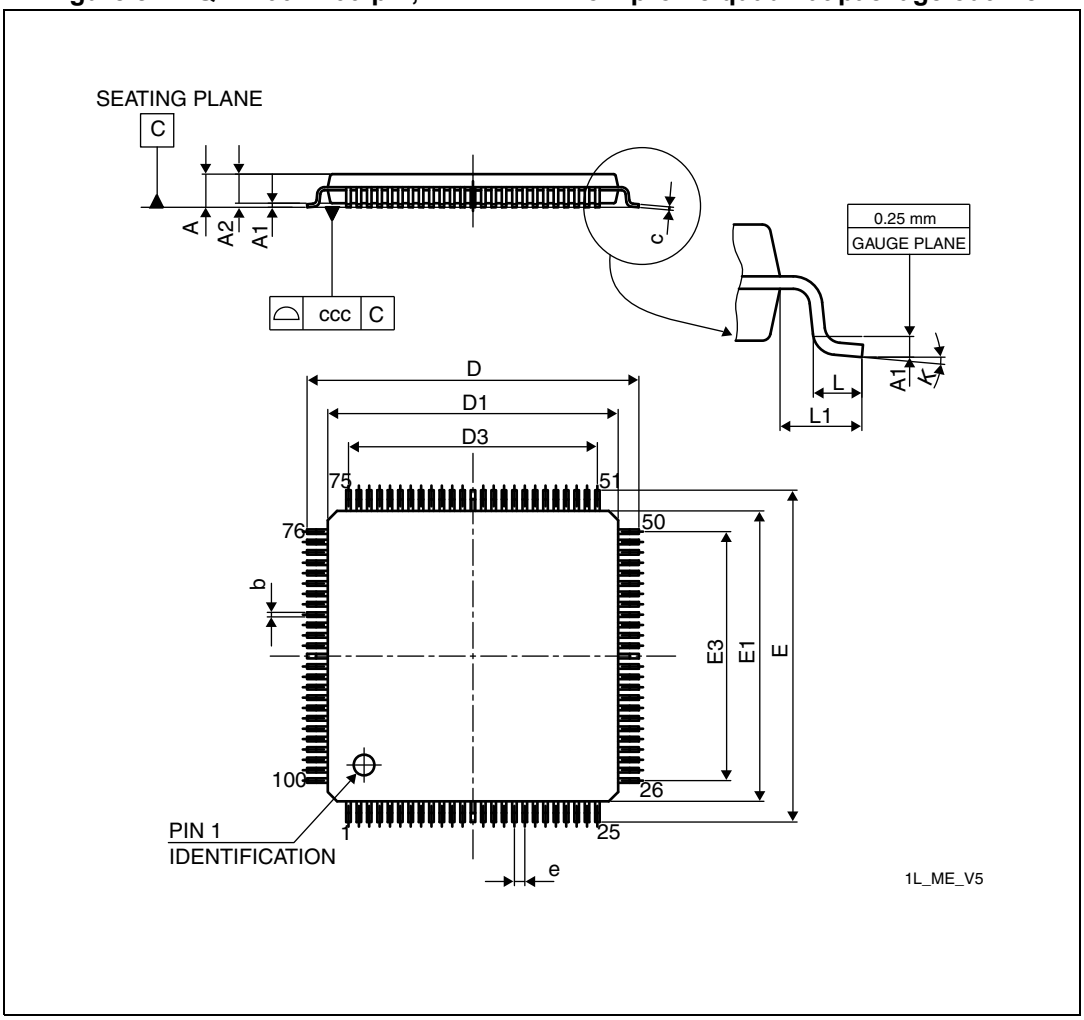


Table 77. Synchronous multiplexed PSRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	$2T_{HCLK}$- 1	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x=0..2)	-	0	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x= 0…2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	2	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	3	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x=16…25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x=16…25)	7	-	ns

7.3 LQFP100 package information

Figure 81. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 90. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591

Table 93. UFBGA176+25, - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 90. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package recommended footprint

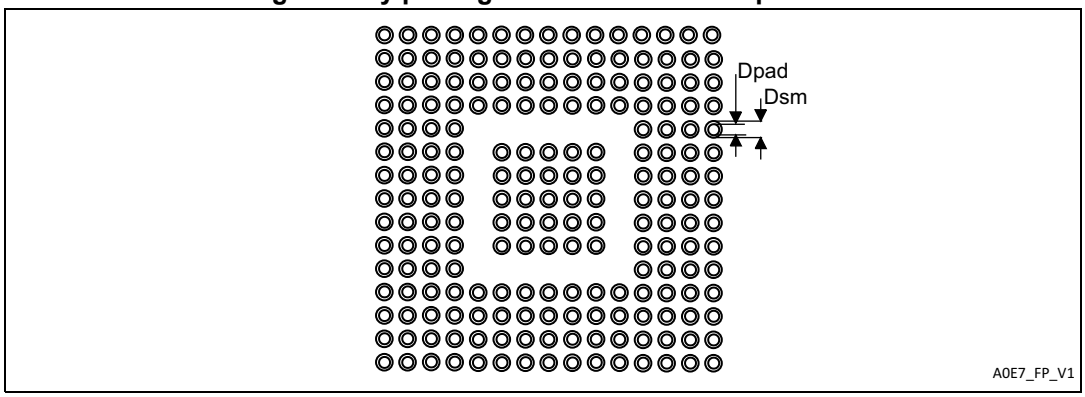


Table 94. UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65 mm
Dpad	0.300 mm
Dsm	0.400 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.300 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm

Table 97. Document revision history (continued)

Date	Revision	Changes
13-Jul-2010	4 (continued)	Added USB OTG_FS features in *Section 3.28: Universal serial bus on-the-go full-speed (OTG_FS)*. Updated V_{CAP_1} and V_{CAP_2} capacitor value to 2.2 µF in *Figure 19: Power supply scheme*. Removed DAC, modified ADC limitations, and updated I/O compensation for 1.8 to 2.1 V range in *Table 15: Limitations depending on the operating power supply range*. Added V_{BORL}, V_{BORM}, V_{BORH} and I_{RUSH} in *Table 19: Embedded reset and power control block characteristics*. Removed table Typical current consumption in Sleep mode with Flash memory in Deep power down mode. Merged typical and maximum current consumption sections and added *Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)*, *Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM, Table 22: Typical and maximum current consumption in Sleep mode, Table 23: Typical and maximum current consumptions in Stop mode, Table 24: Typical and maximum current consumptions in Standby mode*, and *Table 25: Typical and maximum current consumptions in VBAT mode*. Update *Table 34: Main PLL characteristics* and added *Section 6.3.11: PLL spread spectrum clock generation (SSCG) characteristics*. Added *Note 8* for CIO in *Table 48: I/O AC characteristics*. Updated *Section 6.3.18: TIM timer characteristics*. Added T_{NRST_OUT} in *Table 49: NRST pin characteristics*. Updated *Table 52: I2C characteristics*. Removed 8-bit data in and data out waveforms from *Figure 48: ULPI timing diagram*. Removed note related to ADC calibration in *Table 67*. *Section 6.3.20: 12-bit ADC characteristics*: ADC characteristics tables merged into one single table; tables ADC conversion time and ADC accuracy removed. Updated *Table 68: DAC characteristics*. Updated *Section 6.3.22: Temperature sensor characteristics* and *Section 6.3.23: VBAT monitoring characteristics*. Update *Section 6.3.26: Camera interface (DCMI) timing specifications*. Added *Section 6.3.27: SD/SDIO MMC card host interface (SDIO) characteristics*, and *Section 6.3.28: RTC characteristics*. Added *Section 7.7: Thermal characteristics*. Updated *Table 91: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm package mechanical data* and *Figure 86: LQFP176 - Low profile quad flat package 24 × 24 × 1.4 mm, package outline*. Changed tape and reel code to TX in *Table 96: Ordering information scheme*. Added *Table 101: Main applications versus package for STM32F2xxx microcontrollers*. Updated figures in Appendix *A.2: USB OTG full speed (FS) interface solutions* and *A.3: USB OTG high speed (HS) interface solutions*. Updated *Figure 94: Audio player solution using PLL, PLLI2S, USB and 1 crystal* and *Figure 95: Audio PLL (PLLI2S) providing accurate I2S clock*.